

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CE(SUS)} = 70V$ (Min)
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 2.0V$ (Max.) @ $I_C = 5A$

APPLICATIONS

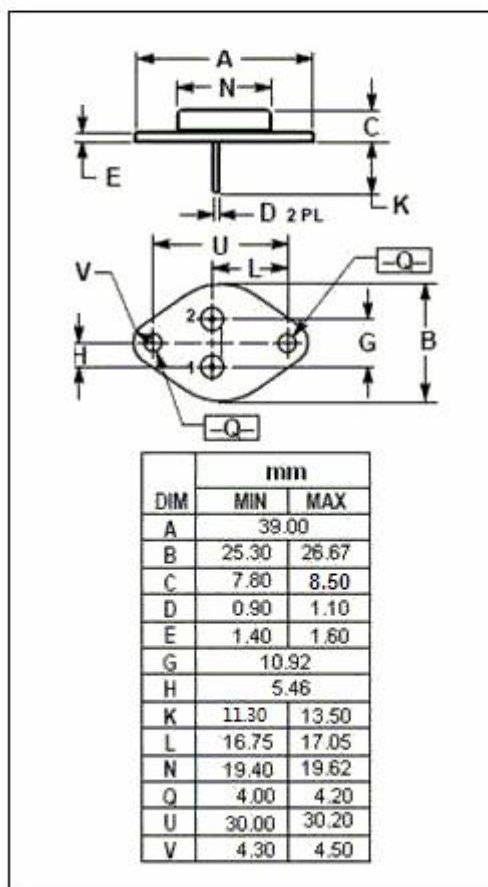
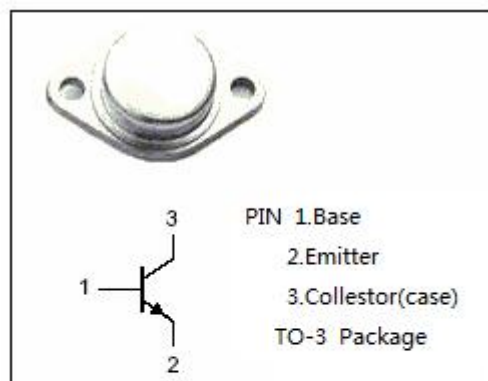
- Designed for use in B/W TV horizontal output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	50	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ C/W$



SPTECH Silicon NPN Power Transistor**2SC681****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	70			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.6A			2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.6A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 200V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	mA
t _f	Fall Time	I _C = 5A; V _{CC} = 25V			0.5	μs